L Number			DB	Time stamp
1	240	The training of training of the training of th	USPAT;	2003/12/09 12:45
		chen-tsung-chuanin. chen-t-c.in.	US-PGPUB;	
		hsu-shew-tsuin. hsu-s-tin.	EPO; JPO;	
7	7122	430 /311 313 314 317 307 300 330 -3	DERWENT	
,	/122	430/311,313,314,317,327,328,330.ccls. 328/694.ccls.	USPAT;	2003/12/09 12:47
		320/094.0018.	US-PGPUB;	
			EPO; JPO;	
2	8	ma-ching-tienin. chen-tsung-chuanin.	DERWENT	00000100100000
-	1	hsu-shew-tsuin.	USPAT;	2003/12/09 12:49
	1	nou onew cou . III.	US-PGPUB;	
	İ		EPO; JPO;	1
3	19	(((resist photoresist photo-resist)	DERWENT USPAT;	0000/10/00 10 50
•		(photosensitive photo-sensitive (sensitive	US-PGPUB;	2003/12/09 12:50
		near (photo light energy radiation))))		
	1	near (duv! (deep adj2 (uv ultraviolet	EPO; JPO; DERWENT	
		ultra-violet ultra adj violet)))) same	DERWENT	
		((oxide dioxide) near (layer film		1
		coating)) same (etchstop etch-stop etch		
		adj stop hardmask hard-mask hard adj mask)		
4	26	(((resist photoresist photo-resist)	HCDAM.	2002/12/22 12 52
-	1 - 50	(photosensitive photo-sensitive (sensitive	USPAT;	2003/12/09 12:50
		near (photo light energy radiation))))	US-PGPUB;	
	i	with cur\$3) and (((resist photoresist	EPO; JPO; DERWENT	
		photo-resist) (photosensitive	DEKMENT	
		photo-sensitive (sensitive near (photo		
		light energy radiation)))) with ((duv!		
		(deep adj2 (uv ultraviolet ultra-violet		
	1	ultra adj violet))) (krf arf f2 "f.sub.2")		
		(("157" "193" "248") near (nm! nanometer		
		nano-meter nano adj meter)))) and		
	,	((etchstop etch-stop etch adj stop		
	1	hardmask hard-mask hard adj mask) with		
		((si silicon si-contain\$3		
	8	silicon-contain\$3) ((silicon adj (nitride		
		oxynitride oxy-nitride oxy adj nitride		
		carbide)) "si.sub.3 n.sub.4" sion sic)))		
	i	and ((oxide dioxide) near (layer film		1
		coating))		
5	7	(((resist photoresist photo-resist)	USPAT;	2003/12/09 12:51
		(photosensitive photo-sensitive (sensitive	US-PGPUB;	2003/12/03 12.51
		near (photo light energy radiation))))	EPO; JPO;	
		near (duv! (deep adj2 (uv ultraviolet	DERWENT	
		near (duv! (deep adj2 (uv ultraviolet ultra-violet ultra adj violet)))) with		
		cur\$3 with (light radiation)		
5	13	(((duv! (deep adj2 (uv ultraviolet	USPAT	2003/12/09 12:52
		ultra-violet ultra adj violet))) ((uv		2003/12/03 12:32
		ultraviolet ultra-violet ultra adj violet)		
)) near3 cur\$3) with temperature with		
		(time seconds! minute)) same (resist		
		photoresist photo-resist)		
3	8673	(duv! uv ultraviolet ultra-violet ultra	USPAT:	2003/12/09 12:53
		adj violet) near3 (resist photoresist	US-PGPUB;	2003/12/03 12:53
		photo-resist)	EPO; JPO;	
		*	DERWENT	
9	7783	(etchstop etch-stop etch adj stop) near	USPAT;	2003/12/09 12:53
		(layer film coating material)	US-PGPUB;	2003/12/09 12:53
		coucking maccital)		
			EPO; JPO;	
10	483449	(si-contain\$3 silicon-contain\$3 (silicon	DERWENT	2002/12/00 12 55
-	100449	adj (oxide dioxide nitride)) sio sio2 sin	USPAT;	2003/12/09 12:55
		sixny si3n4 "sio.sub.2" "si.sub.3 n.sub.4"	US-PGPUB:	
	i	"si.sub.x n.sub.y")	EPO; JPO;	
1	263896	Oxide mean (layer film conting material)	DERWENT	0000 /10 /00 15
~	203070	oxide near (layer film coating material)	USPAT;	2003/12/09 12:55
1				
			US-PGPUB;	ĺ
			EPO; JPO; DERWENT	

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12	2	I (cont. at arcrattoret arcra-violet arcra	USPAT;	2003/12/09	12:56
	1	adj violet) near3 (resist photoresist	US-PGPUB;		
		photo-resist)) same (((etchstop etch-stop	EPO; JPO;		
1		etch adj stop) near (layer film coating	DERWENT		
	i	material)) with ((si-contain\$3			
		silicon-contain\$3 (silicon adj (oxide dioxide nitride)) sio sio2 sin sixny si3n4			
1		"sio.sub.2" "si.sub.3 n.sub.4" "si.sub.x		1	
1	-	n.sub.y"))) same (oxide near (layer film			
	1	coating material))			
13	5	((duv! uv ultraviolet ultra-violet ultra	USPAT;	2003/12/09	12.56
		adj violet) near3 (resist photoresist	US-PGPUB;	2003/12/09	12:30
		photo-resist)) same (((etchstop etch-stop	EPO; JPO;		
		etch adj stop) near (layer film coating	DERWENT		
		material))) same (oxide near (layer film			
	1	coating material))			İ
14	5	(430/311,313,314,317,327,328,330.ccls.	USPAT;	2003/12/09	12:57
İ		328/694.ccls.) and ((duv! uv ultraviolet	US-PGPUB;	1	
		ultra-violet ultra adj violet) near3	EPO; JPO;		
		(resist photoresist photo-resist)) and	DERWENT		
	i	(((etchstop etch-stop etch adj stop) near			
		(layer film coating material)) same			
		((si-contain\$3 silicon-contain\$3 (silicon			
1		adj (oxide dioxide nitride)) sio sio2 sin sixny si3n4 "sio.sub.2" "si.sub.3 n.sub.4"			
		"si.sub.x n.sub.y"))) and (oxide near			
ļ		(layer film coating material))			
	1	(Layer Ilim coating material))			